

EMH2409 — N-Channel Silicon MOSFET

General-Purpose Switching Device

Applications

Features

- The EMH2409 incorporates a N-channel MOSFET that feature low ON-resistance and ultrahigh-speed switching, thereby enabling high-density mounting
- 4V drive
- Halogen free compliance
- Protection diode in

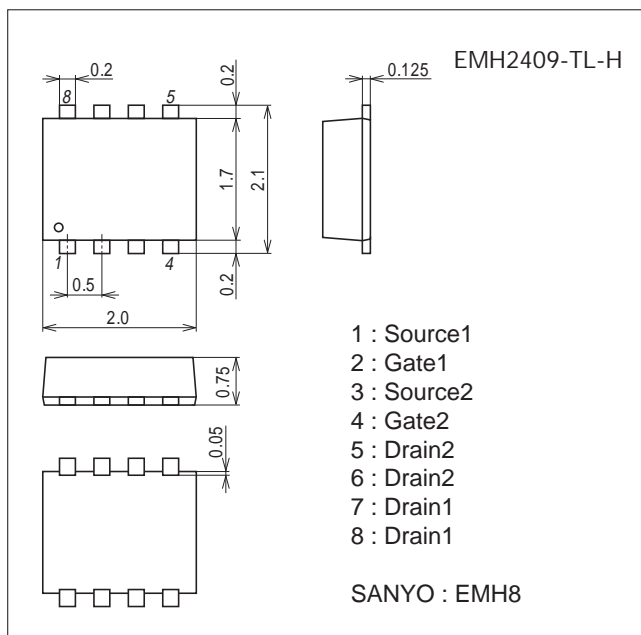
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		30	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		4	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycles≤1%	16	A
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (900mm ² ×0.8mm) 1unit	1.0	W
Total Dissipation	P _T	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.2	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Package Dimensions

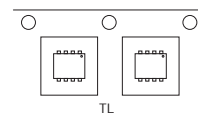
unit : mm (typ)
7045-006



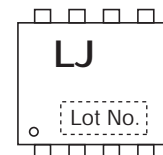
Product & Package Information

- Package : EMH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

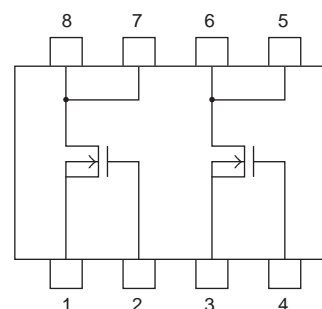
Packing Type : TL



Marking



Electrical Connection

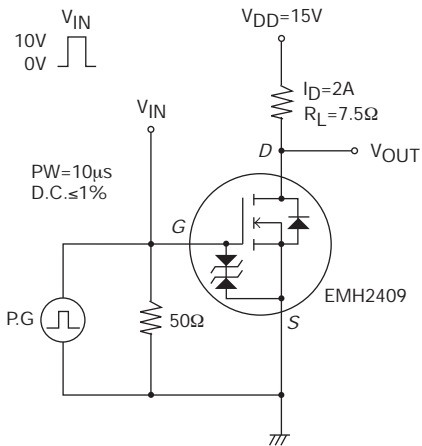


EMH2409

Electrical Characteristics at Ta=25°C

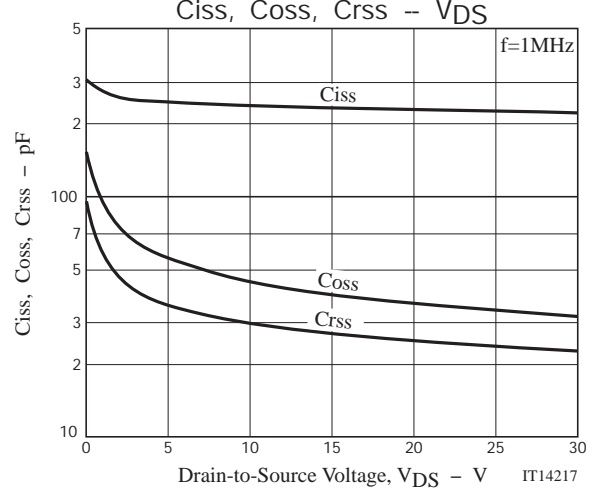
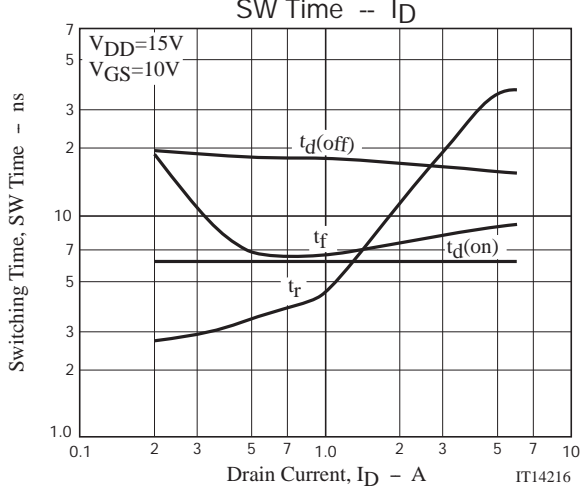
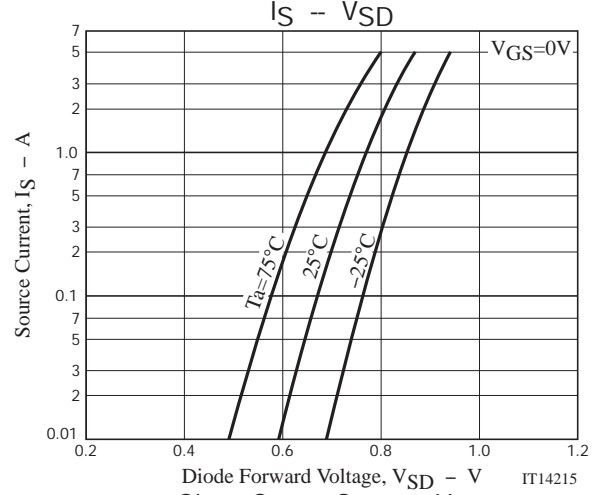
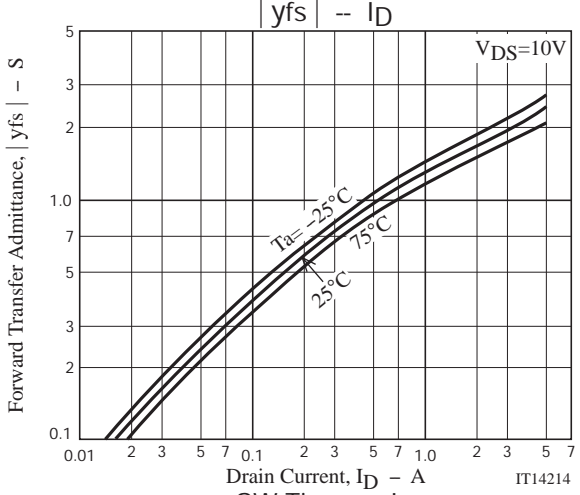
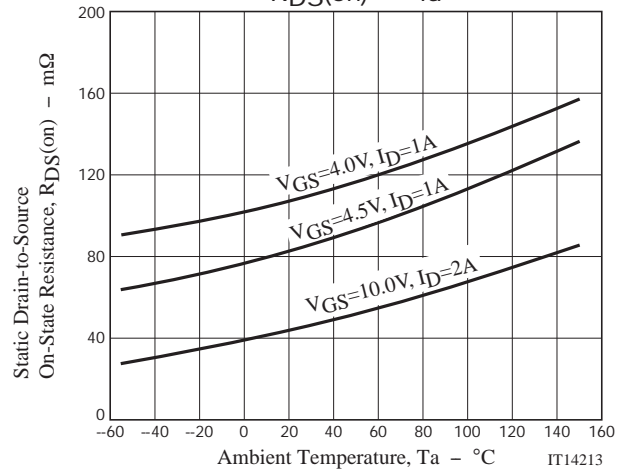
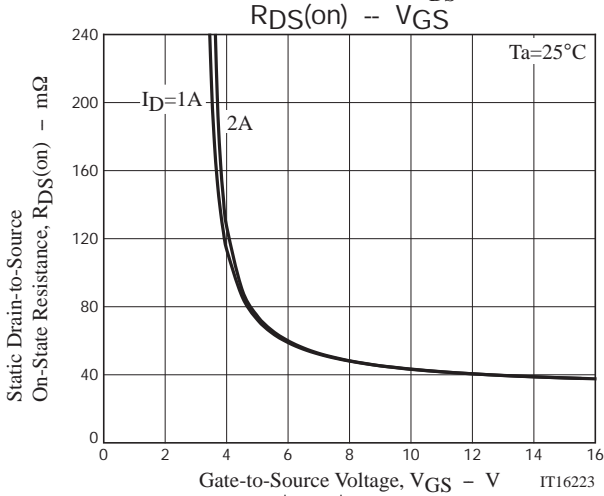
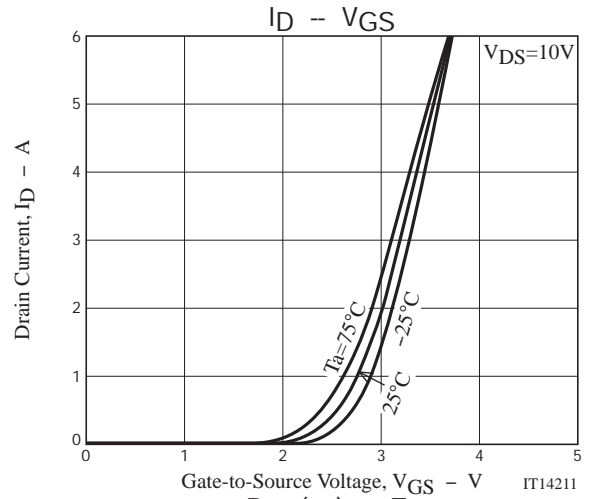
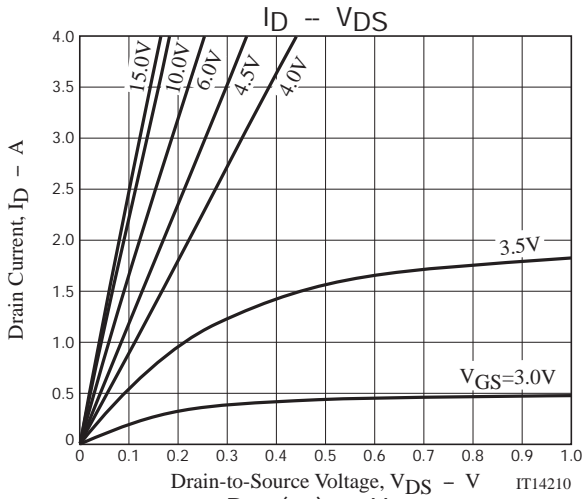
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =2A		1.66		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =2A, V _{GS} =10V		45	59	mΩ
	R _{DS(on)2}	I _D =1A, V _{GS} =4.5V		85	119	mΩ
	R _{DS(on)3}	I _D =1A, V _{GS} =4V		110	155	mΩ
Input Capacitance	C _{iss}	V _{DS} =10V, f=1MHz		240		pF
Output Capacitance	C _{oss}			45		pF
Reverse Transfer Capacitance	C _{rss}			30		pF
Turn-ON Delay Time	t _{d(on)}		See specified Test Circuit.		6.2	
Rise Time	t _r			11		ns
Turn-OFF Delay Time	t _{d(off)}			17		ns
Fall Time	t _f			7.5		ns
Total Gate Charge	Q _g	V _{DS} =15V, V _{GS} =10V, I _D =4A			4.4	
Gate-to-Source Charge	Q _{gs}			1.1		nC
Gate-to-Drain "Miller" Charge	Q _{gd}			0.64		nC
Diode Forward Voltage	V _{SD}		I _S =4A, V _{GS} =0V		0.82	1.2

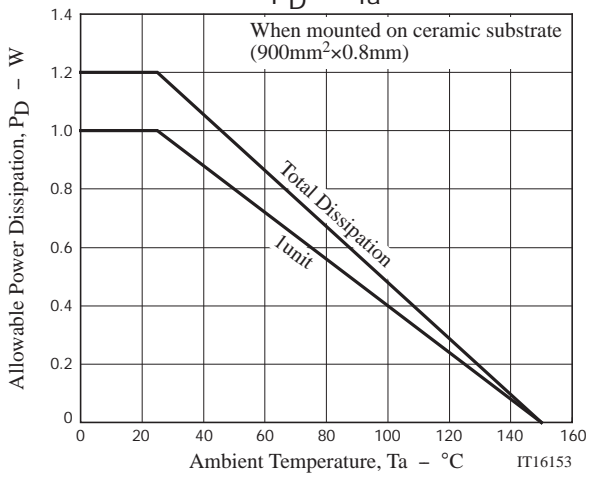
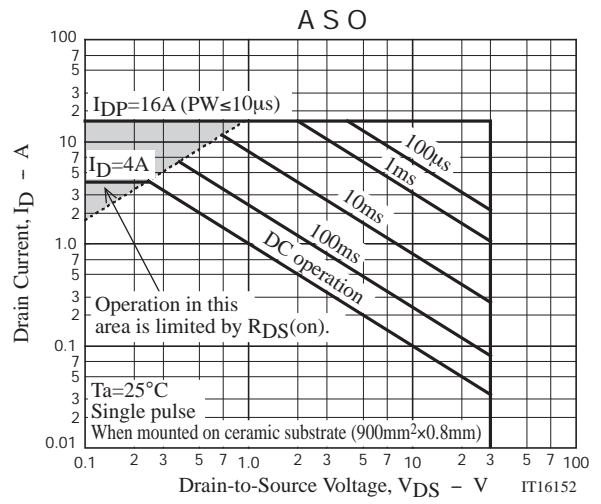
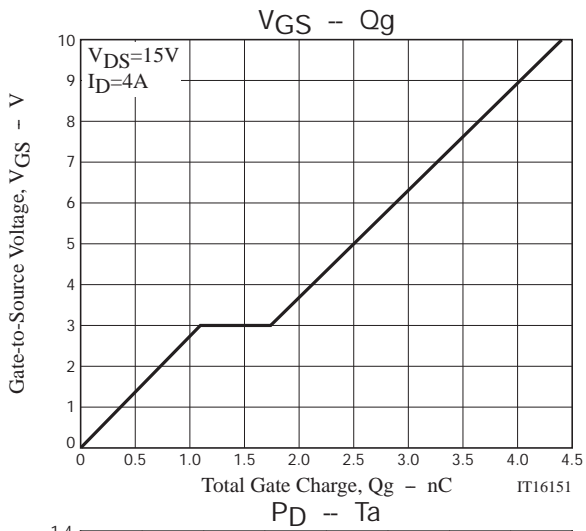
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
EMH2409-TL-H	EMH8	3,000pcs./reel	Pb Free and Halogen Free





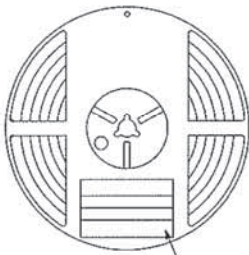
Embossed Taping Specification

EMH2409-TL-H

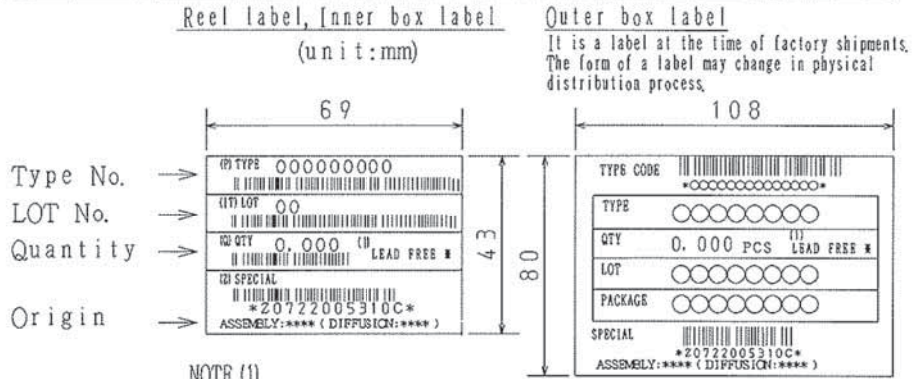
1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
EMH8	MCP4	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method



Reel label



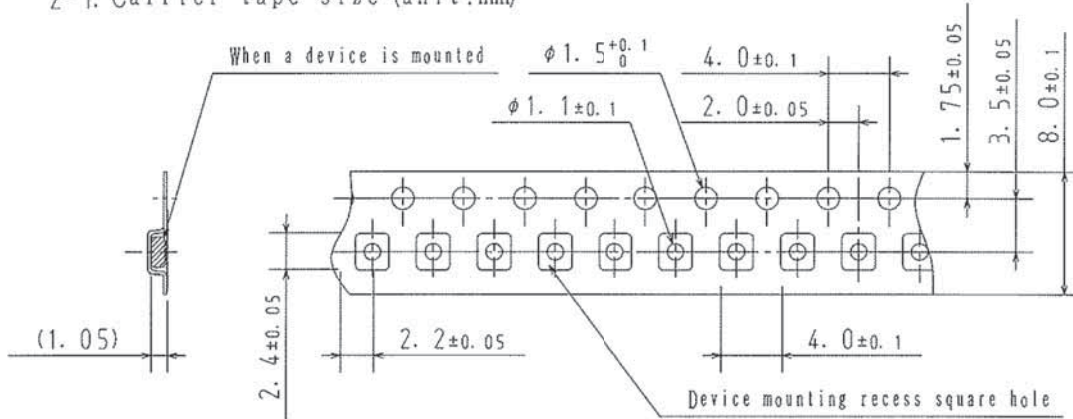
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

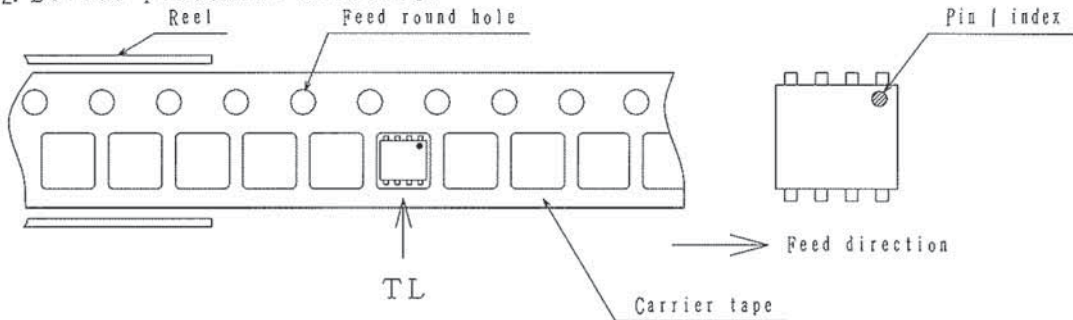
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



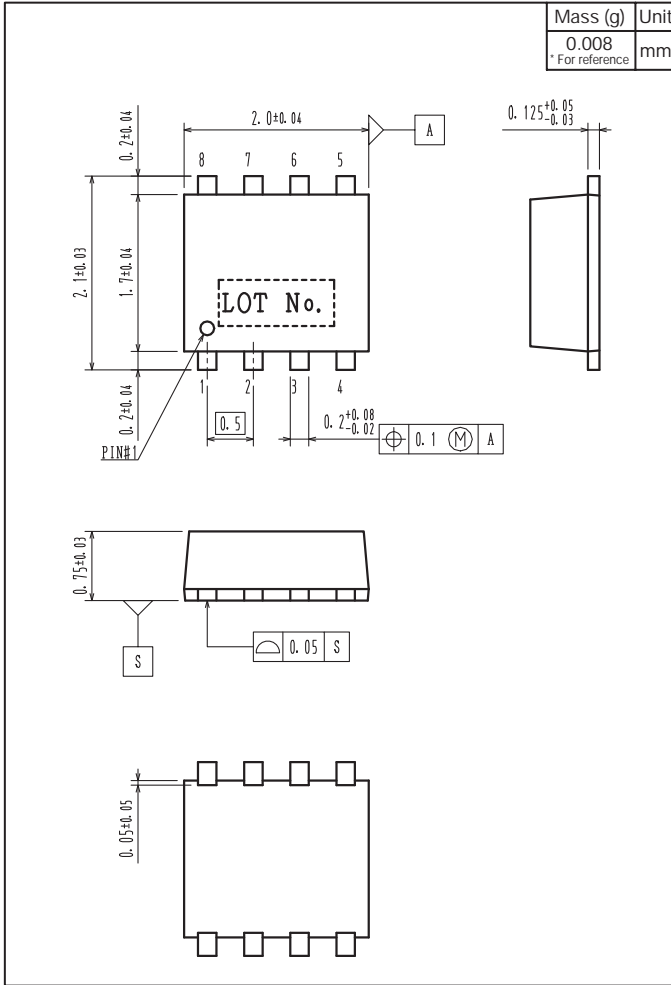
2-2. Device placement direction



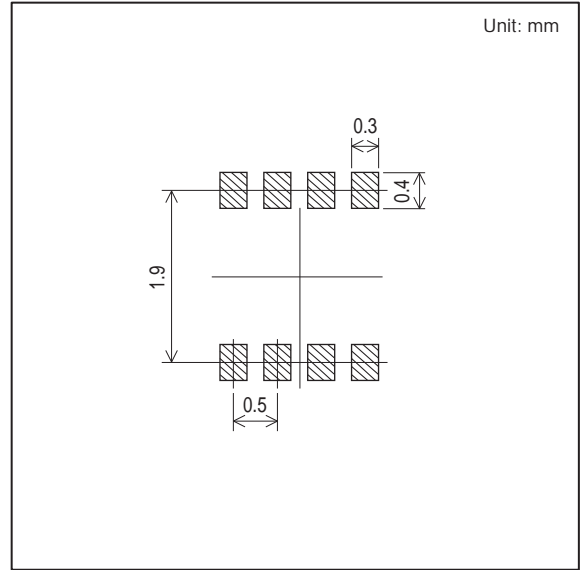
Those with pin | index on the feed hole side.....TL

EMH2409

Outline Drawing EMH2409-TL-H



Land Pattern Example



Note on usage : Since the EMH2409 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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